SEMICONDUCTOR FILM COMPOSITION, METHOD OF MANUFACTURING SEMICONDUCTOR FILM COMPOSITION, METHOD OF MANUFACTURING SEMICONDUCTOR MEMBER, METHOD OF MANUFACTURING SEMICONDUCTOR PROCESSING MATERIAL, AND SEMICONDUCTOR DEVICE

ABSTRACT

A composition for forming a film for semiconductor devices including: a compound (A) including a cationic functional group containing at least one of a primary nitrogen atom or a secondary nitrogen atom and having a weight average molecular weight of from 10,000 to 400,000; a crosslinking agent (B) which includes the three or more -C(=O)OX groups (X is a hydrogen atom or an alkyl group having from 1 to 6 carbon atoms) in the molecule, in which from one to six of three or more -C(=O)OX groups are -C(=O)OH groups, and which has a weight average molecular weight of from 200 to 600; and water (D), in which the compound (A) is an aliphatic amine.